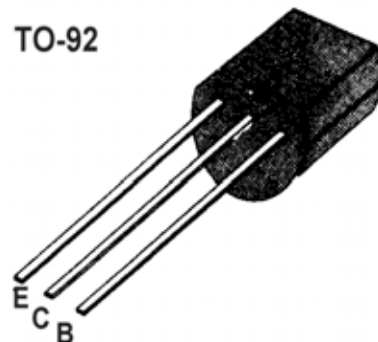


■■APPLICATION: POWER AMPLIFIER APPLICATION, SWITCH APPLICATION.

■■MAXIMUM RATINGS (T_a=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	1.5	A
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	85		300		V _{CE} = 1 V, I _C = 100 mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} = 35 V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 6 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	40			V	I _C = 0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	25			V	I _C = 2 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	6			V	I _B = 0.1 mA, I _C =0
Base-Emitter Voltage	V _{BE}			1	V	V _{CE} = 1 V, I _C = 10 mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.28	0.5	V	I _C = 800 mA, I _B = 80 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.98	1.2	V	I _C = 800 mA, I _B = 80 mA
Gain bandwidth product	f _T	100			MHz	I _C = 50 mA, V _{CE} = 10 V
Common Base Output Capacitance	C _{ob}		9	20	PF	V _{CB} = 10 V, I _E =0, f = 1 MHz

■■h_{FE} Classification

Classification	B	C	D
h _{FE}	85~160	120~200	160~300